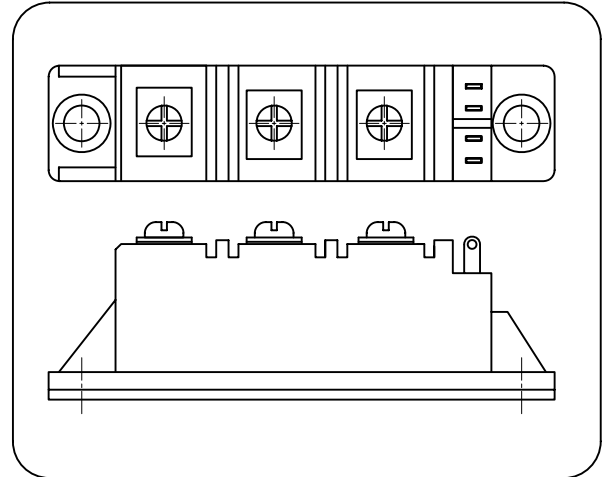


IRK. 26 Series High Voltage Thyristor/ Diode and Thyristor/ Thyristor

FEATURES

- # Electrically isolated base plate.
- # 3500Vrms isolated voltage.
- # Simplified mechanical designs, rapid assembly.
- # Auxiliary cathode terminal for wiring convenience.
- # High surge capability.
- # Wide choice of circuit configuration.
- # Large creepage distance.



DESCRIPTION

These IRK series of Power Modules use power diodes and thyristor in a variety of circuit configuration. The semiconductor chips are electrically isolated from the metal base, allowing common heat sinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges or AC controller. These modules are intended for general purpose applications such as regulated power supplies, lighting circuits and temperature and motor speed control circuit.

MAJOR RATING & CHARACTERISTICS

Parameters	IRK. 26	Units
$I_{T(AV)}$ @Tc-85°C	27	A
$I_{O(RMS)}$	42	A
I_{FSM} @ 50Hz	400	A
I^2t @ 50Hz	800	A ² s
V_{RRM}	400 to 1600	V
T_{STG}	-40 to 125	°C
T_J	-40 to 125	°C

POWER MODULES

IRK. 26 Series

ELECTRICAL SPECIFICATION VOLTAGE RATINGS

Type Number	Voltage Code	V_{RMM} max. repetitive peak reverse and off-state blocking voltage V	V_{RSM} max. Non-repetitive peak reverse voltage V	I_{DRM} / I_{RRM} max. @ 150°C Max. mA
IRK.26	04	400	500	15
	06	600	700	
	08	800	900	
	10	1000	1100	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

ON-STATE CONDUCTION

	Parameter	IRK. 26	Unit	Conditions	
$I_{T(AV)}$	Max, average On-state current (Thyristors)	27	A	180°C conduction, half sine wave $T_c = 85^\circ\text{C}$	
$I_{F(AV)}$	Max, average forward current (Diode)	27	A		
$I_{O(RMS)}$	Max, continuous RMS on-state current	42	A	@ $T_c 85^\circ\text{C}$	
I_{TSM} or I_{FSM}	Max, peak, one cycle non-repetitive on-state or forward current	400	A	$t = 10\text{ms}$	Sinusoidal half wave initial $T_j = T_j \text{ max.}$
I^2t	Maximum I^2t for fusing	800	A^2s	$t = 10\text{ms}$	
		1100	A^2s	$t = 10\text{ms } T_j = 25^\circ\text{C}$	
$V_{T(TO)}$	Max, value of Threshold voltage	0.95	V	$T_j = T_j \text{ max.}$	
r_t	Max, value of on-state slope resistance	40	$\text{m}\Omega$	$T_j = T_j \text{ max,}$	
V_{TM}	Max, peak on-state voltage	1.95	V	$I_{TM} = \pi \times I_{T(AV)}$	$T_j = 25^\circ\text{C}$ 180° conduction
di/dt	Max, non-repetitive rate of rise of turned on current	100	$\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ from. $0.67V_{DRM}$ $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500\text{mA}$ $t_r < 0.5\mu\text{s}$, $t_p > 6\mu\text{s}$	
I_H	Maximum holding current	200	mA	$T_j = 25^\circ\text{C}$. anode supply = 6V resistive load. gate open circuit	
I_L	Max, latching current	400	mA	$T_j = 25^\circ\text{C}$, anode supply = 6V. resistive load	

POWER MODULES

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ELECTRICAL SPECIFICATION TRIGGERING

	Parameter	IRK. 26	Unit	Conditions	
P_{GM}	Max, peak gate power	10	W		
$P_{G(AV)}$	Maximum average gate power	2.5			
I_{GM}	Max, peak gate current	2.5	A		
$-V_{GM}$	Max. peak negative gate voltage	10	V		
V_{GT}	Max, gate voltage required to trigger	2.5	V	$T_j = 25^\circ\text{C}$	Anode supply = 6V resistive load
I_{GT}	Max, gate current required to trigger	150	mA	$T_j = 25^\circ\text{C}$	Anode supply = 6V resistive load
V_{GD}	Max, gate voltage that will not trigger	0.25	V	$T_j = 125^\circ\text{C}$ rated V_{DRM} applied	
I_{GD}	Max, gate current that will not trigger	6.0	mA		

BLOCKING

	Parameter	IRK. 26	Unit	Conditions	
I_{RRM} I_{DRM}	Max. peak reverse and off state leakage current at V_{RRM} V_{DRM}	15	mA	$T_j = 125^\circ\text{C}$, gate open circuit	
V_{INS}	RMS Isolation voltage	3500	V	50Hz, Circuit to base, all terminal shorted, $t=1$ sec.	
dv/dt	Max, critical rate of rise of off-state voltage	1000	V/ μs	$T_j = 125^\circ\text{C}$ linear to 0.67 V_{DRM} gate open circuit	

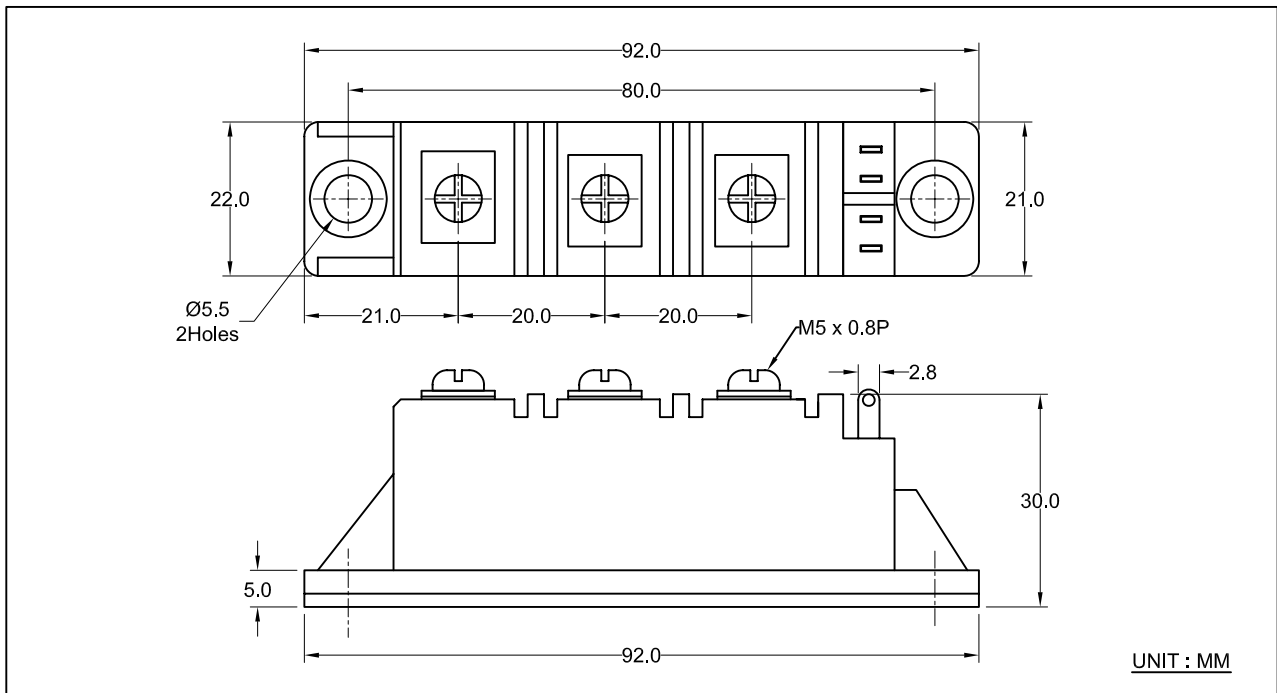
THERMAL AND MECHANICAL SPECIFICATION

	Parameter	IRK. 26	Unit	Conditions	
T_j	Junction operating temperature range	-40 to 125	$^\circ\text{C}$		
T_{stg}	Max, storage temperature range	-40 to 125			
R_{thJ-C}	Max, internal thermal resistance junction to case	0.31	$^\circ\text{C}/\text{W}$	Per module DC operation	
R_{thCS}	Max, thermal resistance, case to heat sink	0.10	$^\circ\text{C}/\text{W}$	Mounting surface flat smooth and greased (per Module)	
T	Mounting torque $\pm 10\%$ Busbar to module	5	Nm	A Mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.	
Wt	Approximate Weight	115	g		
	Case style	To-240AA			

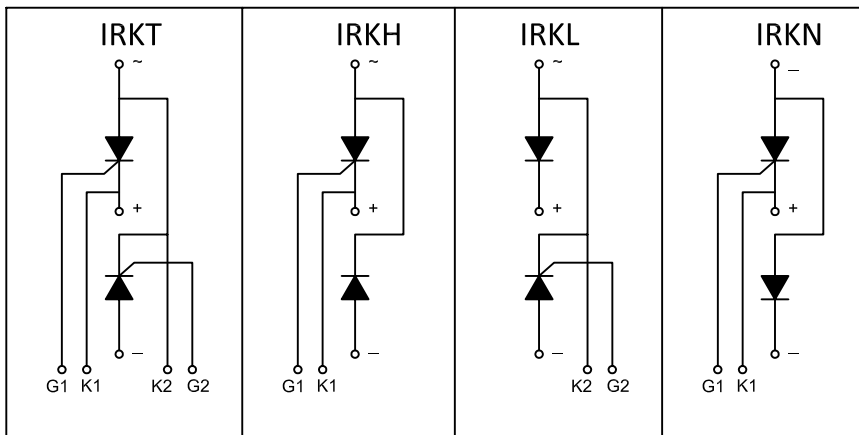
POWER MODULES

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OUTLINE DIAGRAM



CIRCUIT CONFIGURATION TABLE



CIRCUIT CONFIGURATION TABLE

